



# EMIF02-MIC02F1

## 2 LINES EMI FILTER AND ESD PROTECTION

IPAD.™

### MAIN PRODUCT CHARACTERISTICS:

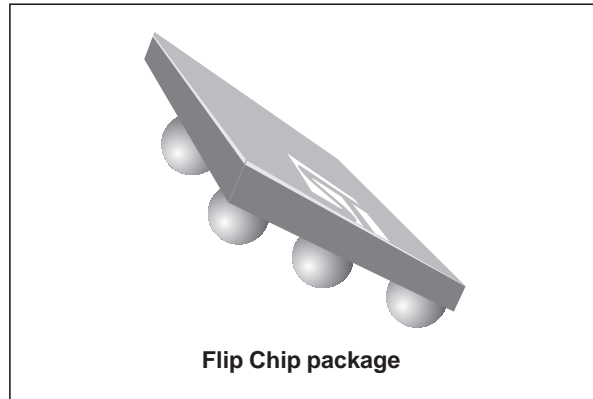
Where EMI filtering in ESD sensitive equipment is required :

- Mobile phones and communication systems
- Computers, printers and MCU Boards

### DESCRIPTION

The EMIF02-MIC02 is a highly integrated devices designed to suppress EMI/RFI noise in all systems subjected to electromagnetic interferences. The EMIF02 flip chip packaging means the package size is equal to the die size.

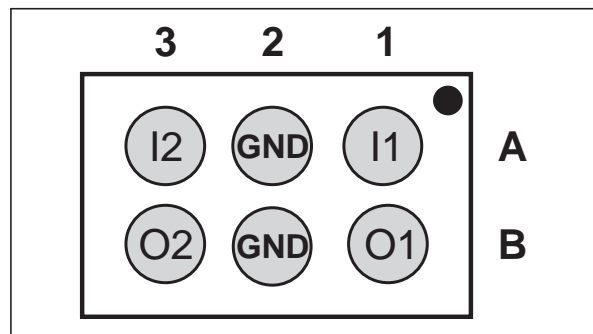
This filter includes an ESD protection circuitry which prevents the device from destruction when subjected to ESD surges up 15kV.



### BENEFITS

- EMI symmetrical (I/O) low-pass filter
- High efficiency in EMI filtering
- Very low PCB space consuming: 1.07mm x 1.57mm
- Very thin package: 0.65 mm
- High efficiency in ESD suppression
- High reliability offered by monolithic integration
- High reducing of parasitic elements through integration & wafer level packaging.

### PIN CONFIGURATION



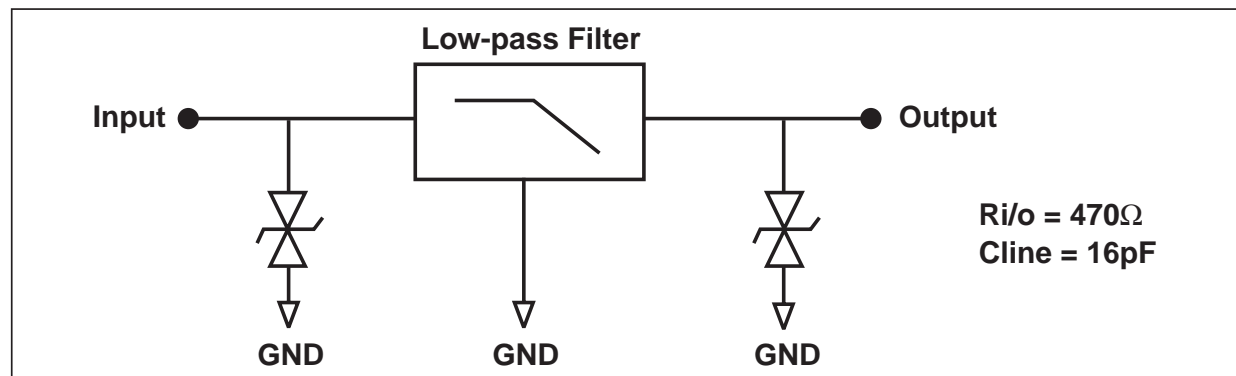
### COMPLIES WITH THE FOLLOWING STANDARDS:

#### IEC61000-4-2

Level 4	on input pins	15kV (air discharge)
		8 kV (contact discharge)
Level 1	on output pins	2kV (air discharge)
		2kV (contact discharge)

#### MIL STD 883E - Method 3015-6 Class 3

### BASIC CELL CONFIGURATION



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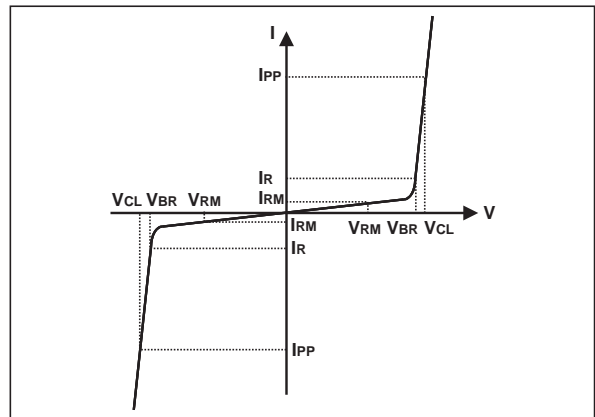
# EMIF02-MIC02F1

## ABSOLUTE RATINGS (limiting values)

Symbol	Parameter and test conditions	Value	Unit
$T_j$	Maximum junction temperature	125	°C
$T_{op}$	Operating temperature range	-40 to + 85	°C
$T_{stg}$	Storage temperature range	125	°C

## ELECTRICAL CHARACTERISTICS ( $T_{amb} = 25\text{ }^\circ\text{C}$ )

Symbol	Parameter
$V_{BR}$	Breakdown voltage
$I_{RM}$	Leakage current @ $V_{RM}$
$V_{RM}$	Stand-off voltage
$V_{CL}$	Clamping voltage
Rd	Dynamic impedance
$I_{PP}$	Peak pulse current
$R_{i/O}$	Series resistance between Input & Output
Cline	Input capacitance per line



Symbol	Test conditions	Min.	Typ.	Max.	Unit
$V_{BR}$	$I_R = 1\text{ mA}$	14	16		V
$I_{RM}$	$V_{RM} = 12\text{ V per line}$			500	$\mu\text{A}$
$R_{i/O}$		423	470	517	$\Omega$
$C_{line}$	@ 0V		16		pF

Fig. 1: S21 (dB) attenuation measurement and Aplac simulation.

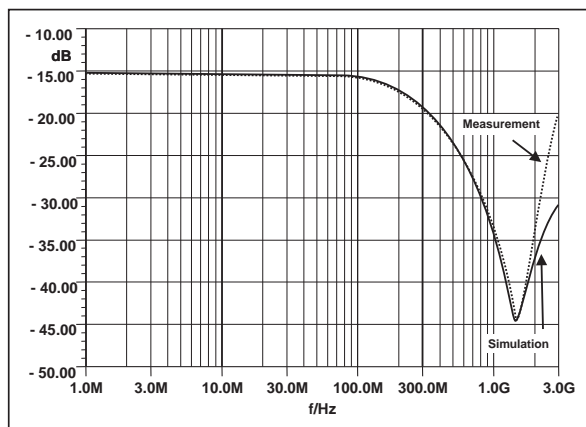
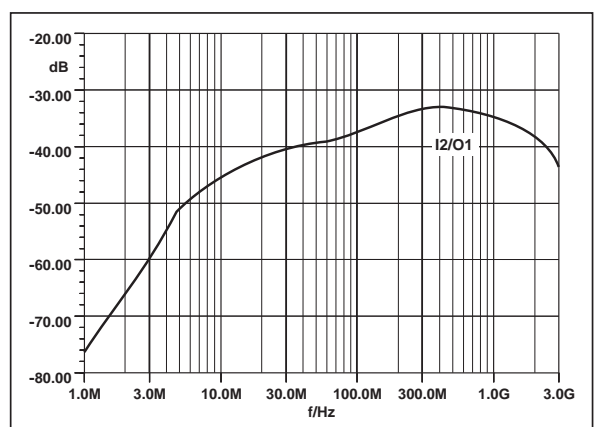
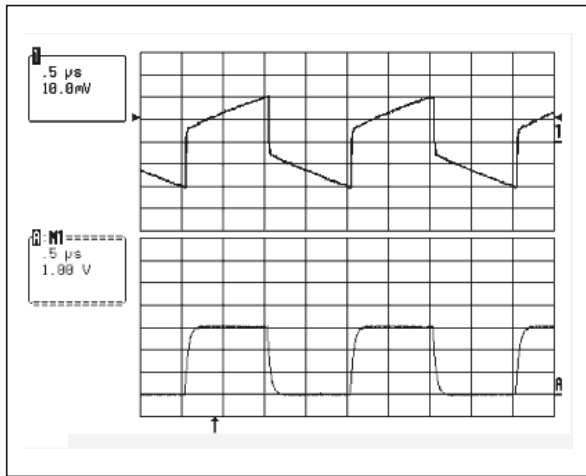


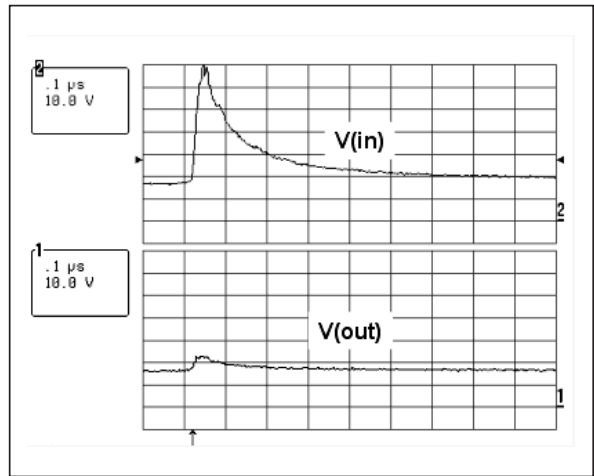
Fig. 2: Analog crosstalk measurements.



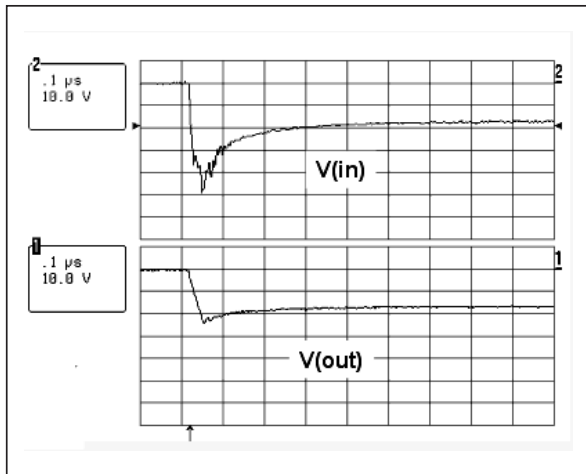
**Fig. 3:** Digital crosstalk measurement



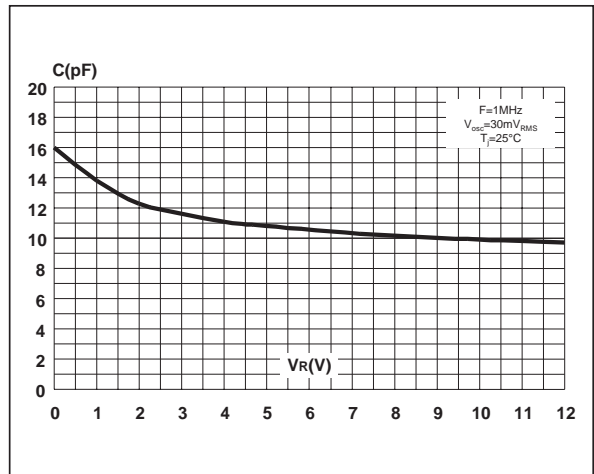
**Fig. 4:** ESD response to IEC61000-4-2 (+15kV air discharge) on one input V(in) and on one output (Vout).



**Fig. 5:** ESD response to IEC61000-4-2 (+15kV air discharge) on one input V(in) and on one output (Vout).

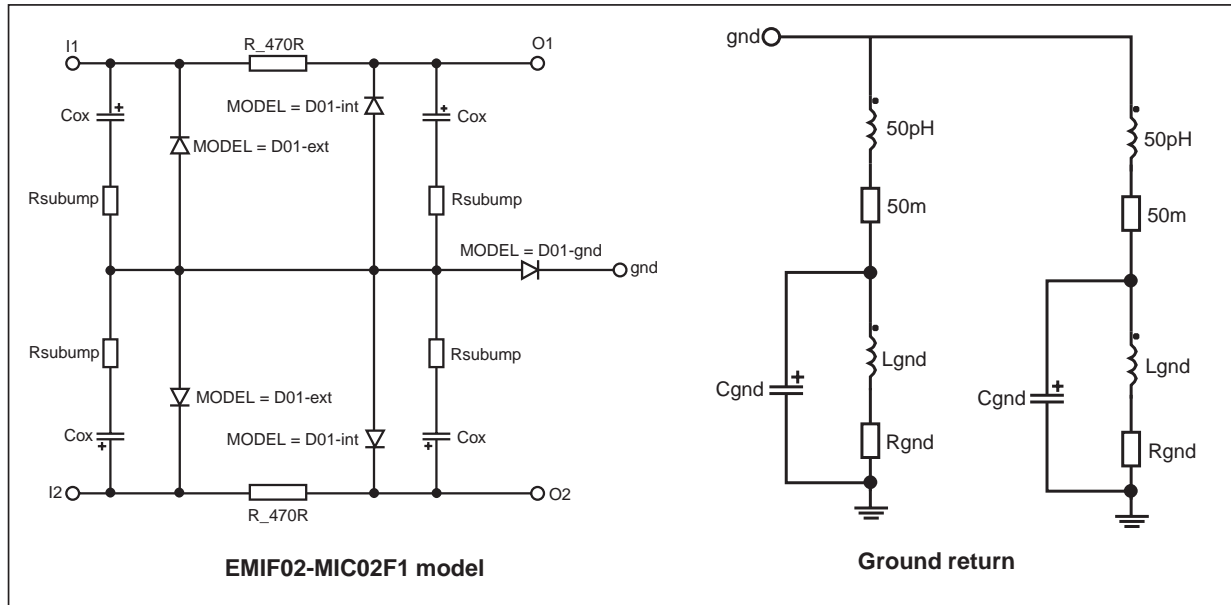


**Fig. 6:** Line capacitance versus applied voltage.



# EMIF02-MIC02F1

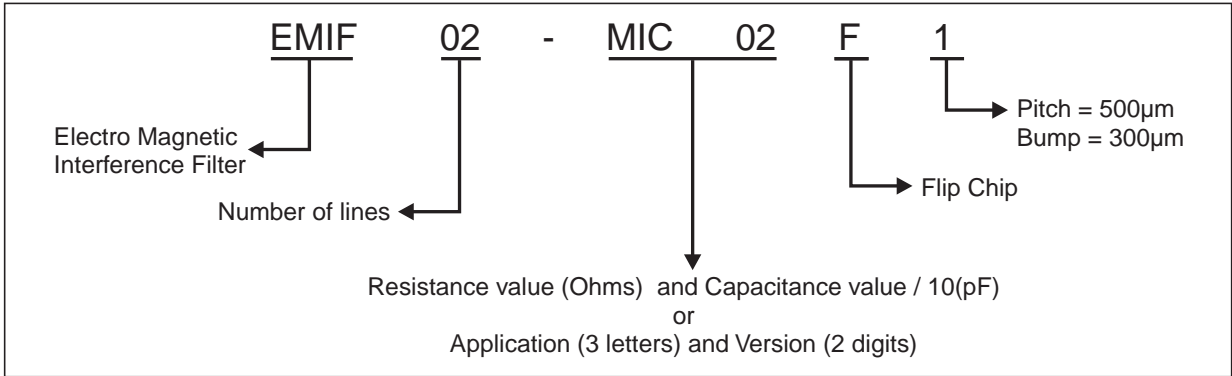
**Fig. 7:** Aplac model



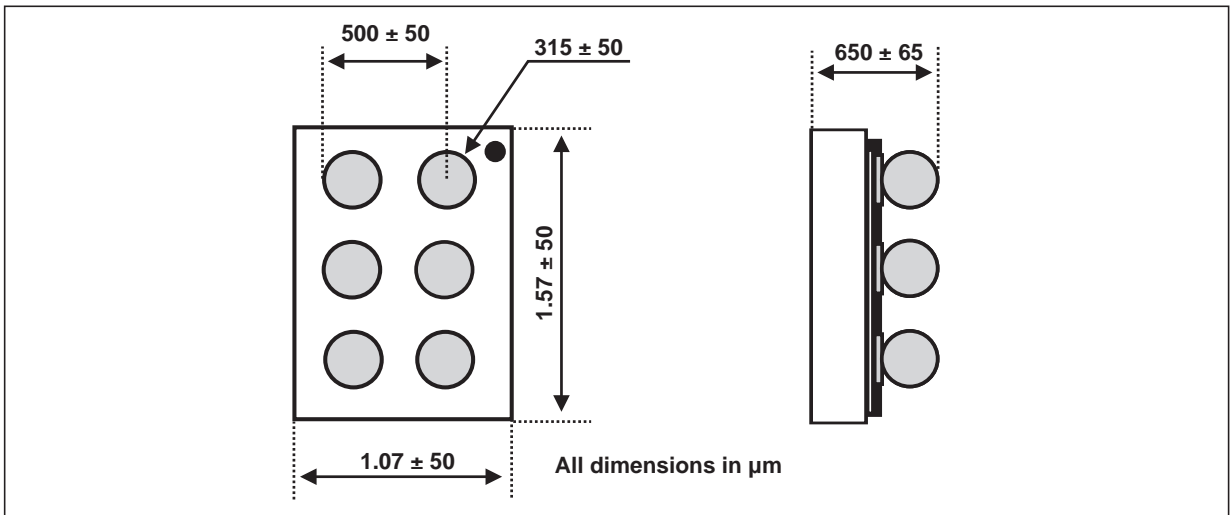
**Fig. 8:** Aplac parameters

Model D01-ext	Model D01-int	Model D01-gnd	aplacvar Ls 400pH
BV = 7	BV = 7	BV = 7	aplacvar Rs 100m
CJO = Cz_ext	CJO = Cz_int	CJO = Cz_gnd	
IBV = 1u	IBV = 1u	IBV = 1u	aplacvar R_470R 482.6
IKF = 1000	IKF = 1000	IKF = 1000	aplacvar Cz_ext 8.73pF
IS = 10f	IS = 10f	IS = 10f	aplacvar Rs_ext 850m
ISR = 100p	ISR = 100p	ISR = 100p	aplacvar Cz_int 2.9pF
N = 1	N = 1	N = 1	aplacvar Rs_int 850m
M = 0.3333	M = 0.3333	M = 0.3333	aplacvar Cz_gnd 215.61pF
RS = Rs_ext	RS = Rs_int	RS = Rs_gnd	aplacvar Rs_gnd 470m
VJ = 0.6	VJ = 0.6	VJ = 0.6	
TT = 50n	TT = 50n	TT = 50n	aplacvar Rgnd 10m
			aplacvar Lgnd 48pH
			aplacvar Cgnd 0.15pF
			aplacvar Cox 3.05pF
			aplacvar Rsubump 200m

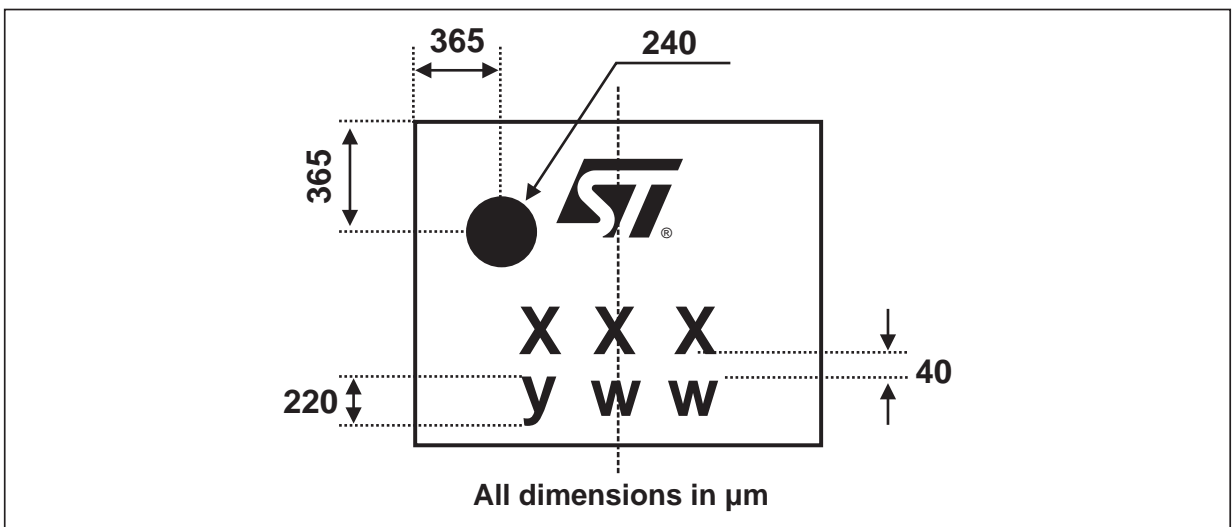
ORDER CODE



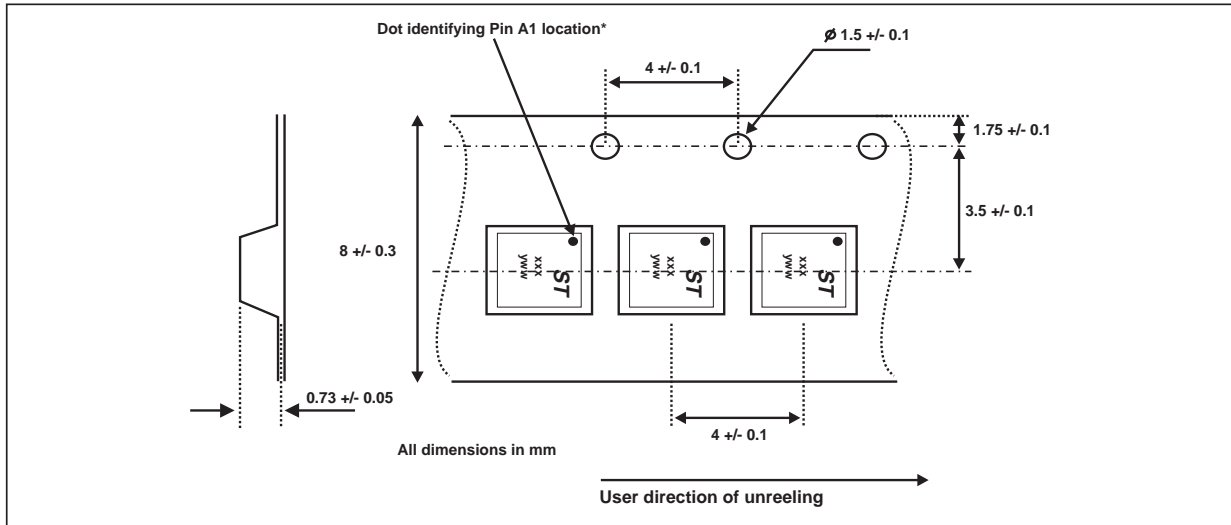
PACKAGE MECHANICAL DATA  
FLIP CHIP



MARKING



PACKING



OTHER INFORMATION

Ordering code	Marking	Package	Weight	Base qty	Delivery mode
EMIF02-MIC02F1	FJT	Flip Chip	2.3 mg	5000	Tape & reel (7")

**Note:** More packing informations are available in the application note AN1235: "Flip-Chip: Package description and recommendations for use"

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